



AMIC

A61L5308 Series

PRELIMINARY

32K X 8 BIT HIGH SPEED CMOS SRAM

Document Title

32K X 8 BIT HIGH SPEED CMOS SRAM

Revision History

<u>Rev. No.</u>	<u>History</u>	<u>Issue Date</u>	<u>Remark</u>
1.0	Initial issue	February 06, 1998	
1.1	Modify 28-pin TSOP package outline drawing and dimensions	June 17, 1998	



A61L5308 Series

PRELIMINARY

32K X 8 BIT HIGH SPEED CMOS SRAM

Features

- Single +3.3V power supply
- Access times: 8/10/12 ns (max.)
- Current: Operating: 150mA (max.)
Standby: 12mA (max.)
- Full static operation, no clock or refreshing required
- All inputs and outputs are directly TTL compatible
- Common I/O using three-state output
- Data retention voltage: 2V (min.)
- Available in 28-pin SOJ and TSOP packages

General Description

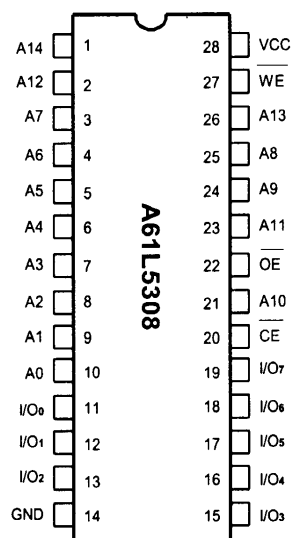
The A61L5308 is a high-speed, low-power 262,144-bit static random access memory organized as 32,768 words by 8 bits and operates on a single 3.3V power supply. It is built using high performance CMOS process. Inputs and three-state outputs are TTL compatible and allow for direct interfacing with common system bus structures.

Minimum standby power is drawn by this device when $\overline{CE}$ is at a high level, independent of the other input levels.

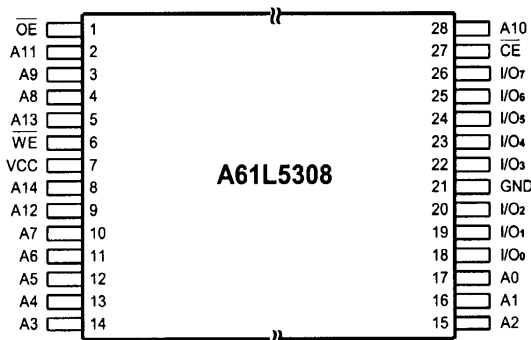
Data retention is guaranteed at a power supply voltage as low as 2V.

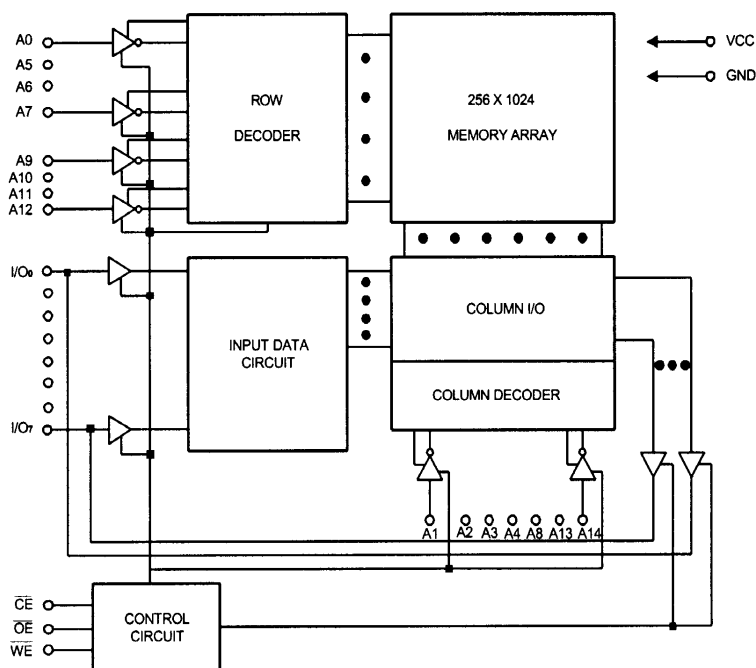
Pin Configurations

■ SOJ



■ TSOP



Block Diagram

Pin Descriptions - SKINNY/SOJ

Pin No.	Symbol	Description
1 - 10, 21, 23 - 26	A0 - A14	Address Inputs
11 - 13, 15 - 19	I/O ₀ - I/O ₇	Data Inputs/Outputs
14	GND	Ground
20	$\overline{CE}$	Chip Enable
22	$\overline{OE}$	Output Enable
27	$\overline{WE}$	Write Enable
28	VCC	Power Supply

Pin Description - TSOP

Pin No.	Symbol	Description
1	$\overline{OE}$	Output Enable
2 - 5, 8 - 17, 28	A0 - A14	Address Input
6	$\overline{WE}$	Write Enable
7	VCC	Power Supply
18 - 20, 22 - 26	I/O ₀ - I/O ₇	Data Inputs/Outputs
21	GND	Ground
27	$\overline{CE}$	Chip Enable

Recommended DC Operating Conditions
 $(T_A = 0^{\circ}\text{C to } +70^{\circ}\text{C})$

Symbol	Parameter	Min.	Typ.	Max.	Unit
VCC	Supply Voltage	3.0	3.3	3.6	V
GND	Ground	0	0	0	V
V _{IH}	Input High Voltage	2.2	-	VCC + 0.3	V
V _{IL}	Input Low (1) Voltage	-0.5	0	+0.8	V
C _L	Output Load	-	-	30	pF

Absolute Maximum Ratings*

VCC to GND -0.5V to +4.6V
 IN, IN/OUT Volt to GND -0.5V to VCC +0.5V
 Operating Temperature, T_{opr} 0°C to +70°C
 Storage Temperature, T_{stg} -55°C to +125°C
 Temperature Under Bias, T_{bias} -10°C to +85°C
 Power Dissipation, P_r 1.0W

***Comments**

Stresses above those listed under "Absolute Maximum Ratings" may cause permanent damage to this device. These are stress ratings only. Functional operation of this device at these or any other conditions above those indicated in the operational sections of this specification is not implied or intended. Exposure to the absolute maximum rating conditions for extended periods may affect device reliability.

DC Electrical Characteristics $(T_A = 0^{\circ}\text{C to } +70^{\circ}\text{C, VCC} = 3.3\text{V} \pm 10\%, \text{GND} = 0\text{V})$

Symbol	Parameter	A61L5308-8/10/12		Unit	Conditions
		Min.	Max.		
I _{LI}	Input Leakage	-	2	μA	V _{IN} = GND to VCC
I _{LO}	Output Leakage	-	2	μA	$\overline{\text{CE}} = V_{IH}$ or $\overline{\text{OE}} = V_{IH}$ V _{IO} = GND to VCC
I _{CC1} (2)	Dynamic Operating Current	-	150	mA	$\overline{\text{CE}} = V_{IL}$, I _{VO} = 0 mA Min. Cycle, Duty = 100%
I _{SB}	Standby Power Supply Current	-	35	mA	$\overline{\text{CE}} = V_{IH}$
I _{SB1}		-	12	mA	$\overline{\text{CE}} \geq \text{VCC} - 0.2\text{V}$ V _{IN} ≥ VCC -0.2V or V _{IN} ≤ 0.2V
V _{OL}	Output Low Voltage	-	0.4	V	I _{OL} = 8 mA
V _{OH}	Output High Voltage	2.4	-	V	I _{OH} = -4 mA

Notes: 1. V_{IL} = -3.0V for pulses less than 20 ns.
 2. I_{CC1} is dependent on output loading, cycle rates, and Read/Write patterns.

Truth Table

Mode	$\overline{CE}$	$\overline{OE}$	$\overline{WE}$	I/O Operation	Supply Current
Standby	H	X	X	High Z	I_{SB}, I_{SB1}
Output Disable	L	H	H	High Z	I_{CC1}
Read	L	L	H	Dout	I_{CC1}
Write	L	X	L	Din	I_{CC1}

Note: X = H or L

Capacitance ($T_A = 25^\circ\text{C}$, $f = 1.0\text{MHz}$)

Symbol	Parameter	Min.	Max.	Unit	Conditions
C_{IN}^*	Input Capacitance		10	pF	$V_{IN} = 0V$
C_{IO}^*	Input/Output Capacitance		10	pF	$V_{IO} = 0V$

* These parameters are sampled and not 100% tested.

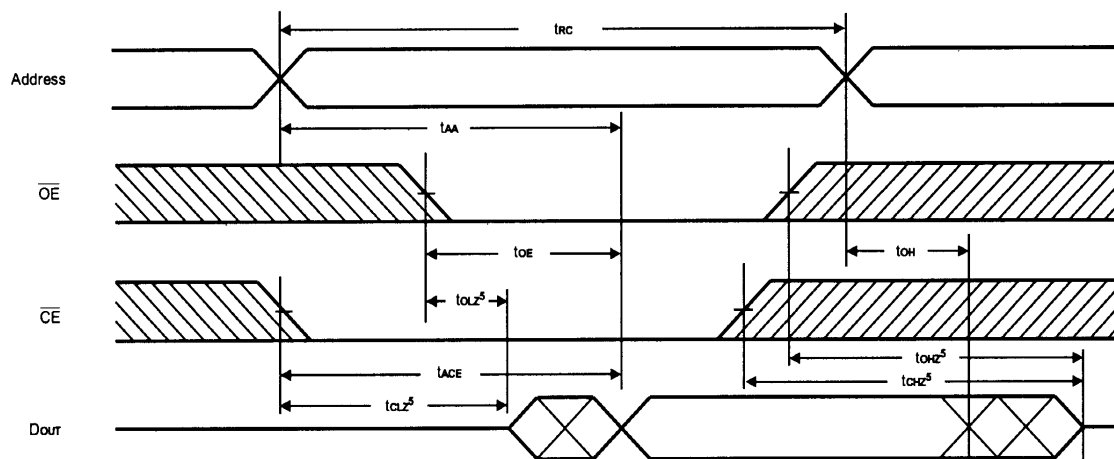
AC Characteristics ($T_A = 0^\circ\text{C}$ to $+70^\circ\text{C}$, $V_{CC} = 3.3V \pm 10\%$)

Symbol	Parameter	A61L5308-8		A61L5308-10		A61L5308-12		Unit
		Min.	Max.	Min.	Max.	Min.	Max.	
Read Cycle								
trc	Read Cycle Time	8	-	10	-	12	-	ns
tAA	Address Access Time	-	8	-	10	-	12	ns
tACE	Chip Enable Access Time	-	8	-	10	-	12	ns
toE	Output Enable to Output Valid	-	4	-	5	-	6	ns
tclZ	Chip Enable to Output in Low Z	3	-	3	-	3	-	ns
tolZ	Output Enable to Output in Low Z	0	-	0	-	0	-	ns
tchZ	Chip Disable Output in High Z	0	4	0	5	0	6	ns
tohZ	Output Disable to Output in High Z	0	4	0	5	0	6	ns
toH	Output Hold from Address Change	3	-	3	-	3	-	ns

AC Characteristics (continued)

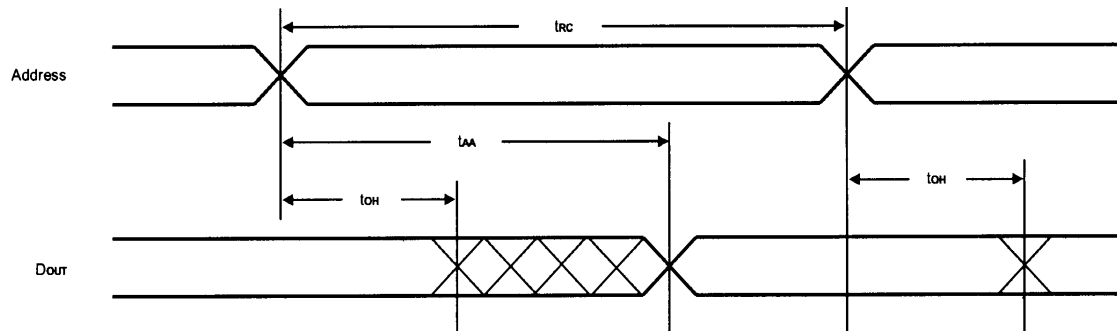
Symbol	Parameter	A61L5308-8		A61L5308-10		A61L5308-12		Unit
		Min.	Max.	Min.	Max.	Min.	Max.	
Write Cycle								
t _{wc}	Write Cycle Time	8	-	10	-	12	-	ns
t _{cw}	Chip Enable to End of Write	8	-	9	-	10	-	ns
t _{as}	Address Setup Time of Write	0	-	0	-	0	-	ns
t _{aw}	Address Valid to End of Write	8	-	9	-	10	-	ns
t _{wp}	Write Pulse Width	8	-	9	-	10	-	ns
t _{wr}	Write Recovery Time	0	-	0	-	0	-	ns
t _{whz}	Write to Output in High Z	0	4	0	5	0	6	ns
t _{dw}	Data to Write Time Overlap	4	-	5	-	6	-	ns
t _{dh}	Data Hold from Write Time	0	-	0	-	0	-	ns
t _{ow}	Output Active from End of Write	3	-	3	-	3	-	ns

Notes: t_{chz}, t_{ohz} and t_{whz} are defined as the time at which the outputs achieve the open circuit condition and are not referred to output voltage levels.

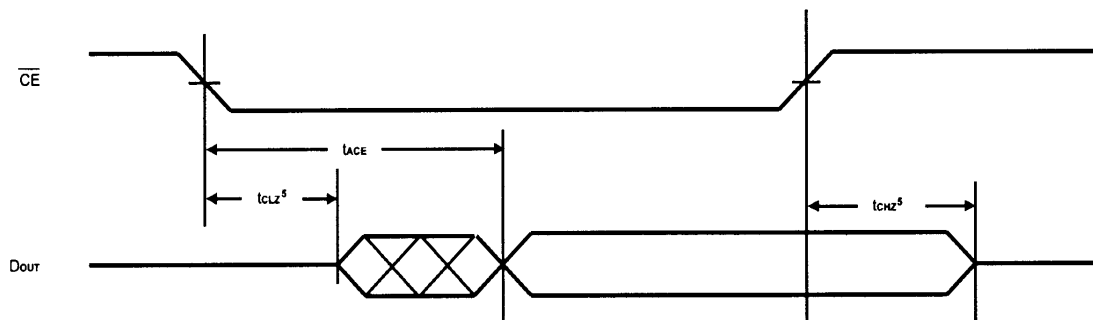
Timing Waveforms
Read Cycle 1⁽¹⁾


Timing Waveforms (continued)

Read Cycle 2^(1, 2, 4)



Read Cycle 3^(1, 3, 4)



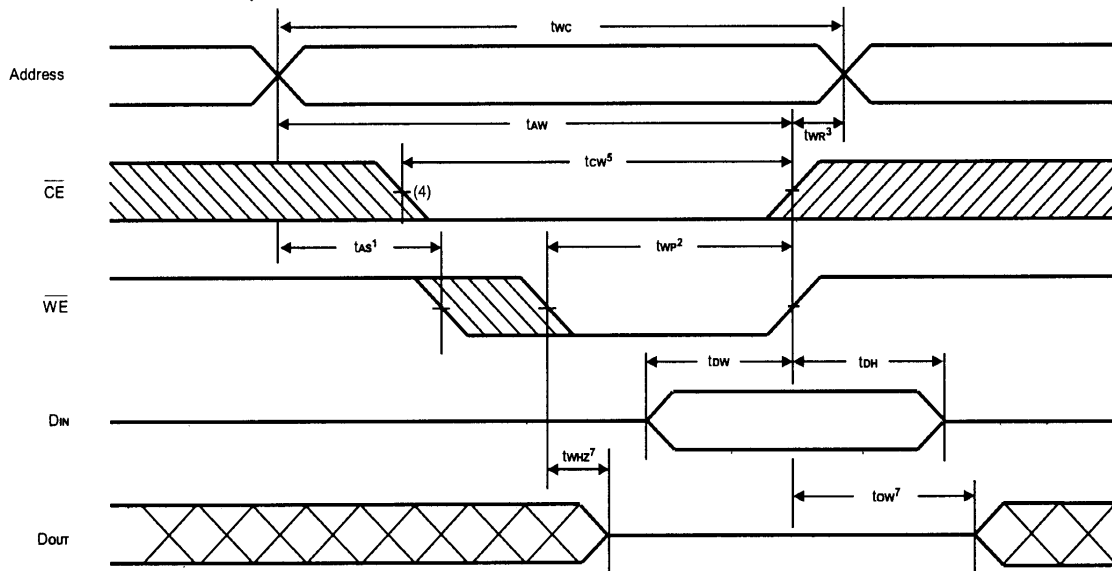
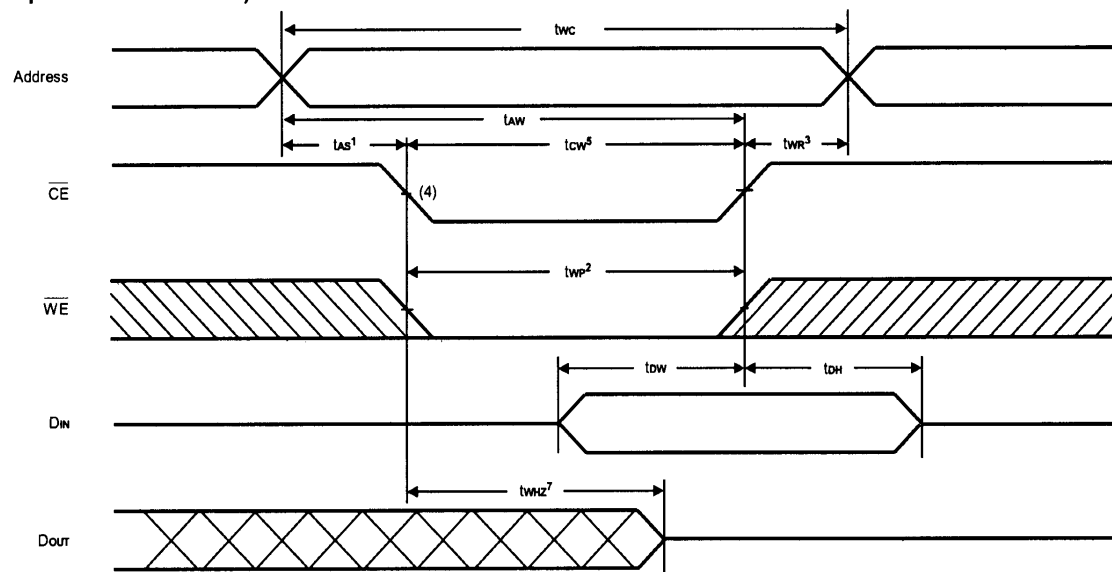
Notes: 1. $\overline{WE}$ is high for Read Cycle.

2. Device is continuously enabled, $\overline{CE} = V_{IL}$.

3. Address valid prior to or coincident with $\overline{CE}$ transition low.

4. $\overline{OE} = V_{IL}$.

5. Transition is measured $\pm 200\text{mV}$ from steady state. This parameter is sampled and not 100% tested.

Timing Waveforms (continued)
Write Cycle 1⁽⁶⁾
(Write Enable Controlled)

Write Cycle 2
(Chip Enable Controlled)


Notes: 1. t_{AS} is measured from the address valid to the beginning of Write.

2. A Write occurs during the overlap (t_{WP}) of a low $\overline{CE}$ and a low $\overline{WE}$.

3. t_{WR} is measured from the earliest of $\overline{CE}$ or $\overline{WE}$ going high to the end of the Write cycle.

4. If the $\overline{CE}$ low transition occurs simultaneously with the $\overline{WE}$ low transition or after the $\overline{WE}$ transition, outputs remain in a high impedance state.

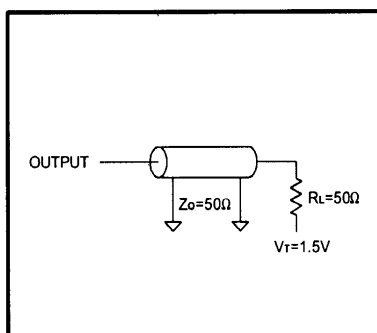
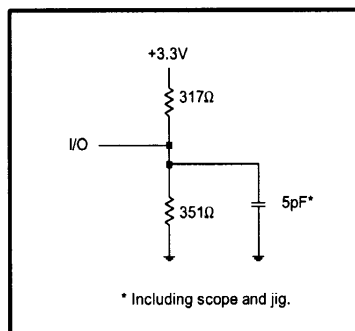
5. t_{CW} is measured from the later of $\overline{CE}$ going low to the end of Write.

6. $\overline{OE}$ is continuously low. ($\overline{OE} = V_{IL}$)

7. Transition is measured $\pm 200\text{mV}$ from steady state. This parameter is sampled and not 100% tested.

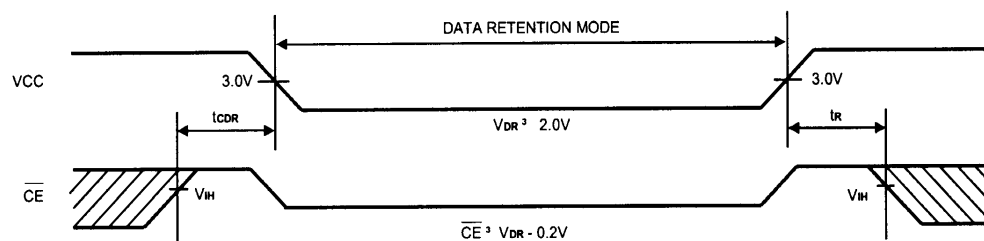
AC Test Conditions

Input Pulse Levels	0V to 3.0V
Input Rise and Fall Time	2 ns
Input and Output Timing Reference Levels	1.5V
Output Load	See Figures 1 and 2


Figure 1. Output Load

Figure 2. Output Load for t_{CLZ} , t_{OLZ} , t_{CHZ} , t_{OHZ} , t_{WHZ} , and t_{OW}
Data Retention Characteristics ($T_A = 0^\circ\text{C}$ to 70°C)

Symbol	Parameter	Min.	Max.	Unit	Conditions
V_{DR}	VCC for Data Retention	2	3.6	V	$\overline{CE} \geq V_{CC} - 0.2V$
I_{CCDR}	Data Retention Current	-	12	mA	$V_{CC} = 2.0V$ $\overline{CE} \geq V_{CC} - 0.2V$ $V_{IN} \geq V_{CC} - 0.2V$ or $V_{IN} \leq 0.2V$
t_{CDR}	Chip Disable to Data Retention Time	0	-	ns	See Retention Waveform
t_R	Operation Recovery Time	t_{RC}^*	-	ns	

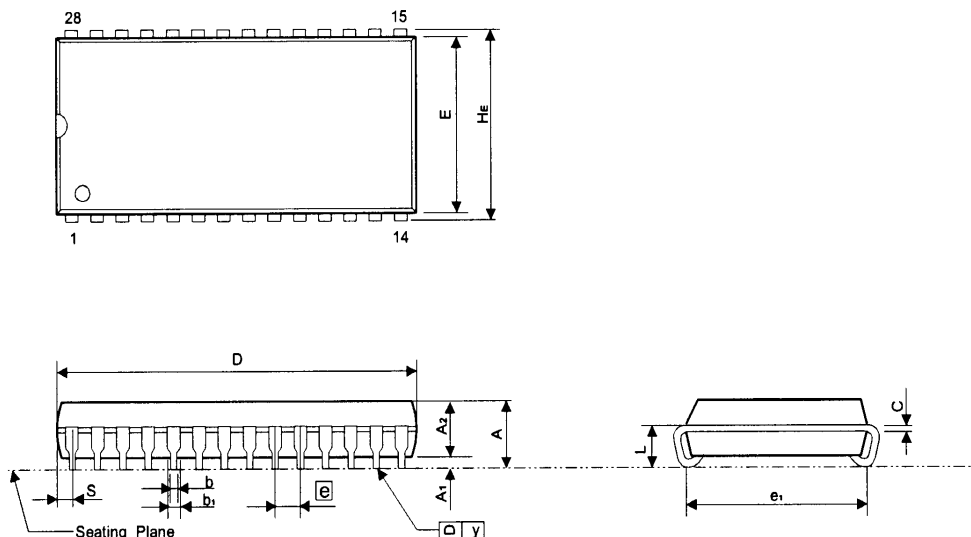
t_{RC} = Read Cycle Time

Low VCC Data Retention Waveform

Ordering Information

Part No.	Access Time (ns)	Operating Current Max. (mA)	Standby Current Max. (mA)	Package
A61L5308S-8	8	150	12	28L SOJ
A61L5308S-10	10	150	12	28L SOJ
A61L5308S-12	12	150	12	28L SOJ
A61L5308V-8	8	150	12	28L TSOP
A61L5308V-10	10	150	12	28L TSOP
A61L5308V-12	12	150	12	28L TSOP

Package Information
SOJ 28L Outline Dimensions

unit: inches/mm



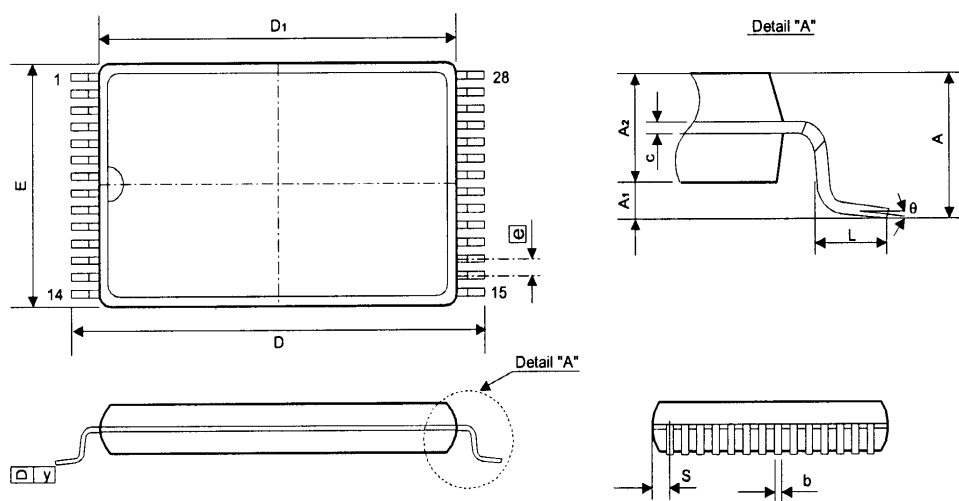
Symbol	Dimensions in inches			Dimensions in mm		
	Min	Nom	Max	Min	Nom	Max
A	-	-	0.140	-	-	3.56
A1	0.027	-	-	0.69	-	-
A2	0.095	0.100	0.105	2.41	2.54	2.67
b1	0.028 TYP			0.71 TYP		
b	0.018 TYP			0.46 TYP		
C	0.010 TYP			0.25 TYP		
D	-	0.710	0.730	-	18.03	18.54
E	0.295	0.300	0.305	7.49	7.62	7.75
e	0.050 BSC			1.27 BSC		
e1	0.255	0.265	0.275	6.48	6.73	6.99
HE	0.329	0.337	0.345	8.36	8.56	8.76
L	0.077	0.087	0.097	1.96	2.21	2.46
S	-	-	0.045	-	-	1.14
y	-	-	0.004	-	-	0.10

Notes:

1. The maximum value of dimension D includes end flash.
2. Dimension E does not include resin fins.
3. Dimension e1 is for PC Board surface mount pad pitch design reference only.
4. Dimension S includes end flash.

Package Information
TSOP 28L TYPE I (8 X 13.4mm) Outline Dimensions

unit: inches/mm



Symbol	Dimensions in inches			Dimensions in mm		
	Min	Nom	Max	Min	Nom	Max
A	-	-	0.049	-	-	1.25
A1	0.002	-	-	0.05	-	-
A2	0.037	0.039	0.041	0.95	1.00	1.05
b	0.007	0.009	0.011	0.17	0.22	0.27
c	0.005	-	0.008	0.12	-	0.21
E	0.311	0.315	0.319	7.90	8.00	8.10
L	0.012	0.020	0.028	0.30	0.50	0.70
D	0.520	0.528	0.536	13.20	13.40	13.60
D1	0.461	0.465	0.469	11.70	11.80	11.90
	0.022 BSC			0.55 BSC		
S	0.017 TYP			0.425 TYP		
y	-	-	0.004	-	-	0.10
θ	0°	-	5°	0°	-	5°

Notes:

1. The maximum value of dimension D1 includes end flash.
2. Dimension E does not include resin fins.
3. Dimension S includes end flash.